

UTC 8050S NPN EPITAXIAL SILICON TRANSISTOR

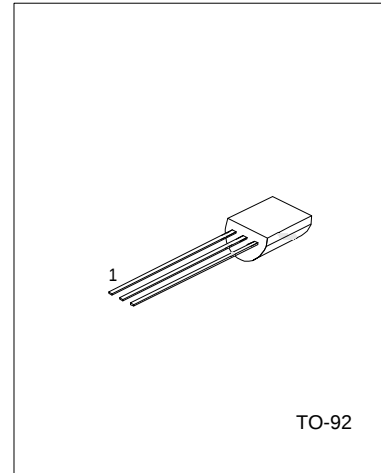
LOW VOLTAGE HIGH CURRENT SMALL SIGNAL NPN TRANSISTOR

DESCRIPTION

The UTC8050S is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

FEATURES

- *Collector current up to 800mA
- *Collector-Emitter voltage up to 20 V
- *Complementary to UTC 8550S



1:EMITTER 2: COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Dissipation(Ta=25℃)	P _c	1	W
Collector Current	I _c	800	mA
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CB0}	I _c =100μA,I _E =0	30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c =1mA,I _B =0	20			V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _E =100μA,I _c =0	5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =30V,I _E =0			1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5V,I _c =0			100	nA
DC Current Gain(note)	h _{FE}	V _{CE} =1V,I _c =1mA V _{CE} =1V,I _c =150 mA V _{CE} =1V,I _c =500mA	100 120 40	110	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c =500mA,I _B =50mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c =500mA,I _B =50mA			1.2	V
Base-Emitter Saturation Voltage	V _{BE}	V _{CE} =1V,I _c =10mA			1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =10V,I _c =50mA	100			MHz
Output Capacitance	C _{ob}	V _{CB} =10V,I _E =0 f=1MHz		9.0		pF

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CLASSIFICATION OF hFE

RANK	C	D	E
RANGE	120-200	160-300	280-400

TYPICAL PERFORMANCE CHARACTERISTICS

